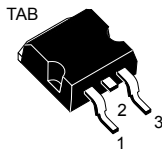
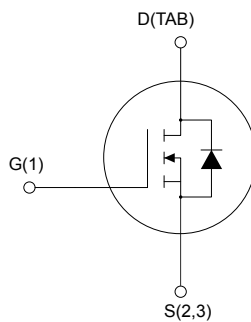


## Silicon carbide Power MOSFET 1200 V, 42 A, 90 mΩ (typ., $T_J=150\text{ °C}$ ), in an H<sup>2</sup>PAK-2 package


 H<sup>2</sup>PAK-2


NCHG1DTABS23



### Features

- Very tight variation of on-resistance vs temperature
- Very high operating temperature capability ( $T_J = 175\text{ °C}$ )
- Very fast and robust intrinsic body diode
- Low capacitance

### Applications

- Solar inverters, UPS
- Motor drives
- High voltage DC-DC converters
- Switch mode power supplies

### Description

This silicon carbide Power MOSFET is produced exploiting the advanced, innovative properties of wide bandgap materials. This results in unsurpassed on-resistance per unit area and very good switching performance almost independent of temperature. The outstanding thermal properties of the SiC material allow designers to use an industry-standard outline with significantly improved thermal capability. These features render the device perfectly suitable for high-efficiency and high power density applications.

#### Product status link

[SCT30N120H](#)

#### Product summary

<b>Order code</b>	SCT30N120H
<b>Marking</b>	SCT30N120
<b>Package</b>	H <sup>2</sup> PAK-2
<b>Packing</b>	Tape and reel

# 1 Electrical ratings

**Table 1. Absolute maximum ratings**

Symbol	Parameter	Value	Unit
$V_{DS}$	Drain-source voltage	1200	V
$V_{GS}$	Gate-source voltage	-10 to 25	V
$I_D$	Drain current (continuous) at $T_C = 25\text{ °C}$ (limited by die)	42	A
$I_D$	Drain current (continuous) at $T_C = 100\text{ °C}$	30	A
$I_{DM}^{(1)}$	Drain current (pulsed)	90	A
$P_{TOT}$	Total power dissipation at $T_C = 25\text{ °C}$	230	W
$T_{stg}$	Storage temperature range	-55 to 175	°C
$T_j$	Operating junction temperature range		°C

1. Pulse width limited by safe operating area.

**Table 2. Thermal data**

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	0.65	°C/W
$R_{thj-pcb}^{(1)}$	Thermal resistance junction-pcb	35	°C/W

1. When mounted on 1 inch<sup>2</sup> FR-4 board, 2 oz Cu.

## 2 Electrical characteristics

( $T_{CASE} = 25\text{ °C}$  unless otherwise specified).

**Table 3. On/off states**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$I_{DSS}$	Zero gate voltage drain current	$V_{DS} = 1200\text{ V}; V_{GS} = 0\text{ V}$		1	25	$\mu\text{A}$
$I_{GSS}$	Gate-body leakage current	$V_{DS} = 0\text{ V}; V_{GS} = -10\text{ to }22\text{ V}$			$\pm 100$	nA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}, I_D = 1\text{ mA}$	1.8	3.5		V
$R_{DS(on)}$	Static drain-source on- resistance	$V_{GS} = 20\text{ V}, I_D = 20\text{ A}$		80	100	$\text{m}\Omega$
		$V_{GS} = 20\text{ V}, I_D = 20\text{ A}, T_J = 150\text{ °C}$		90		$\text{m}\Omega$

**Table 4. Dynamic**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$C_{iss}$	Input capacitance	$V_{DS} = 400\text{ V}, f = 1\text{ MHz}, V_{GS} = 0\text{ V}$	-	1700	-	pF
$C_{oss}$	Output capacitance		-	130	-	pF
$C_{rss}$	Reverse transfer capacitance		-	25	-	pF
$Q_g$	Total gate charge	$V_{DD} = 800\text{ V}, I_D = 20\text{ A}, V_{GS} = 0\text{ to }20\text{ V}$	-	105	-	nC
$Q_{gs}$	Gate-source charge		-	16	-	nC
$Q_{gd}$	Gate-drain charge		-	40	-	nC
$R_g$	Gate input resistance	$f = 1\text{ MHz open drain}$	-	5	-	$\Omega$

**Table 5. Switching energy (inductive load)**

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$E_{on}$	Turn-on switching energy	$V_{DD} = 800\text{ V}, I_D = 20\text{ A}, R_G = 6.8\text{ }\Omega, V_{GS} = -2\text{ to }20\text{ V}$	-	500	-	$\mu\text{J}$
$E_{off}$	Turn-off switching energy		-	350	-	$\mu\text{J}$
$E_{on}$	Turn-on switching energy	$V_{DD} = 800\text{ V}, I_D = 20\text{ A}, R_G = 6.8\text{ }\Omega, V_{GS} = -2\text{ to }20\text{ V}, T_J = 150\text{ °C}$	-	500	-	$\mu\text{J}$
$E_{off}$	Turn-off switching energy		-	400	-	$\mu\text{J}$

**Table 6. Switching times**

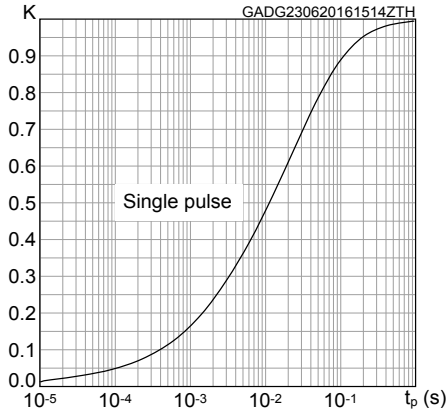
Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 800\text{ V}, I_D = 20\text{ A}, R_G = 0\text{ }\Omega, V_{GS} = -2\text{ to }20\text{ V}$	-	19	-	ns
$t_f$	Fall time		-	28	-	ns
$t_{d(off)}$	Turn-off delay time		-	45	-	ns
$t_r$	Rise time		-	20	-	ns

**Table 7. Reverse SiC diode characteristics**

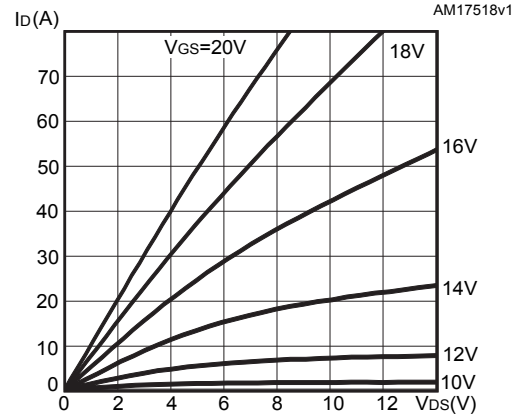
Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$V_{SD}$	Diode forward voltage	$I_F = 10\text{ A}$ , $V_{GS} = 0\text{ V}$	-	3.5	-	V
$t_{rr}$	Reverse recovery time	$I_{SD} = 20\text{ A}$ , $di/dt = 100\text{ A}/\mu\text{s}$ $V_{DD} = 800\text{ V}$	-	140		ns
$Q_{rr}$	Reverse recovery charge		-	140	-	nC
$I_{RRM}$	Reverse recovery current		-	2	-	A

## 2.1 Electrical characteristics (curves)

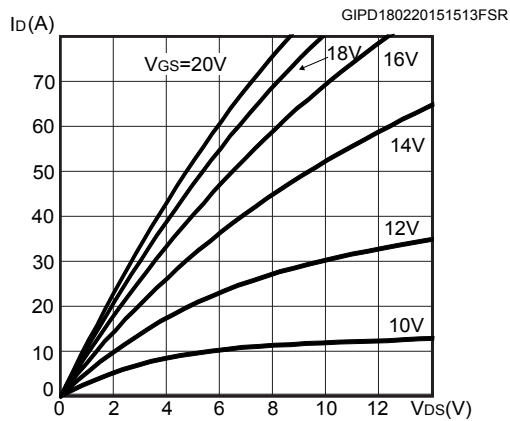
**Figure 1. Normalized thermal impedance**



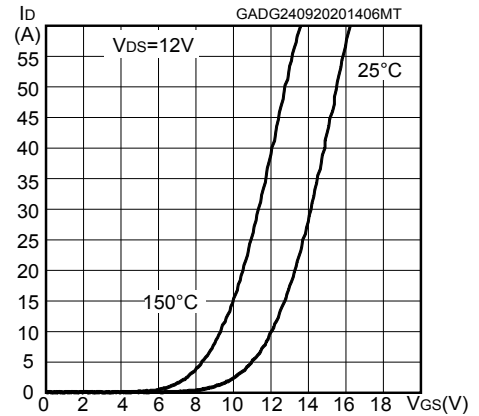
**Figure 2. Output characteristics ( $T_J = 25^\circ\text{C}$ )**



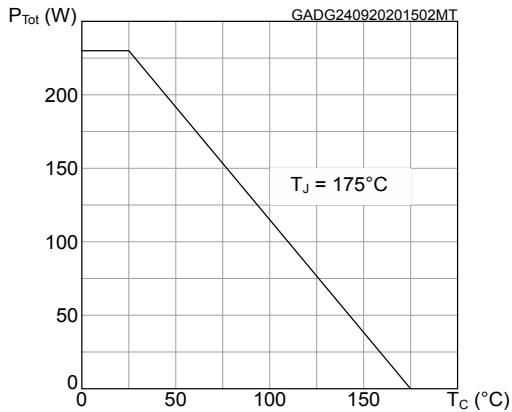
**Figure 3. Output characteristics ( $T_J = 150^\circ\text{C}$ )**



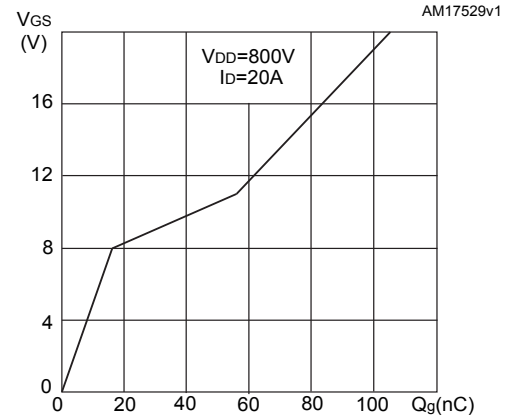
**Figure 4. Transfer characteristics**



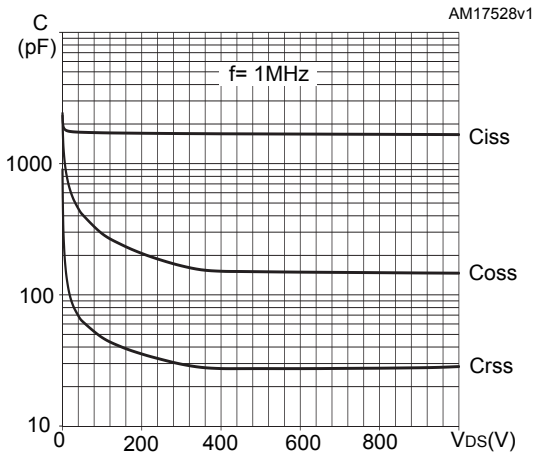
**Figure 5. Total power dissipation**



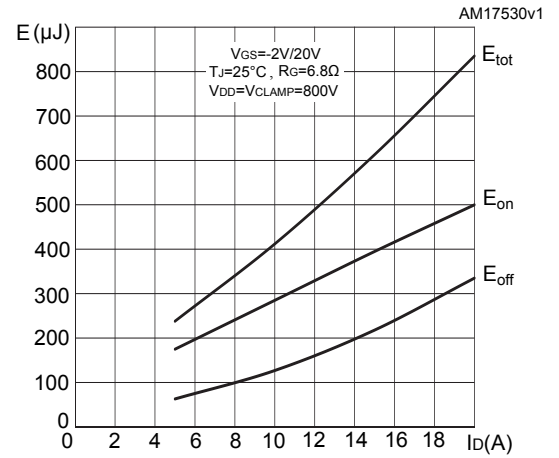
**Figure 6. Gate charge vs gate-source voltage**



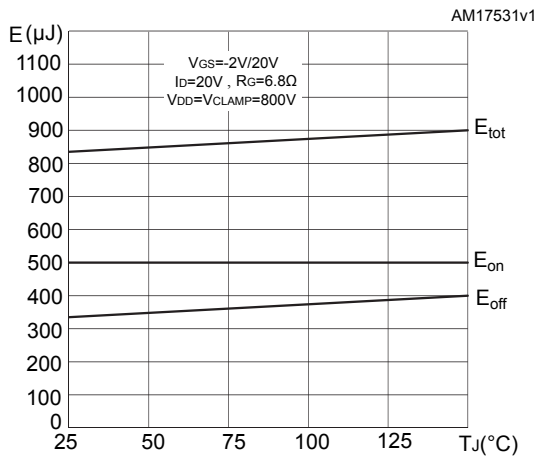
**Figure 7. Capacitance variations**



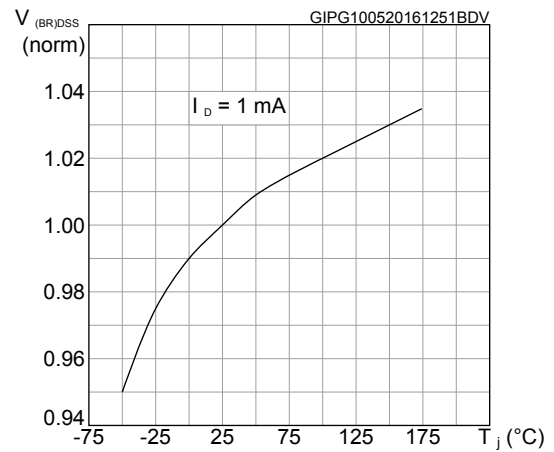
**Figure 8. Switching energy vs drain current**



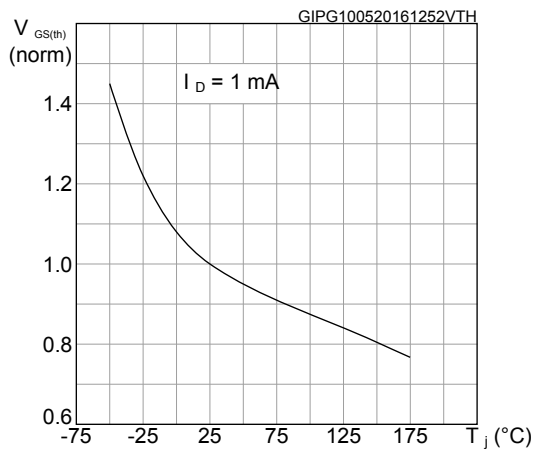
**Figure 9. Switching energy vs junction temperature**



**Figure 10. Normalized V<sub>(BR)DSS</sub> vs temperature**



**Figure 11. Normalized gate threshold voltage vs temperature**



**Figure 12. Normalized on-resistance vs temperature**

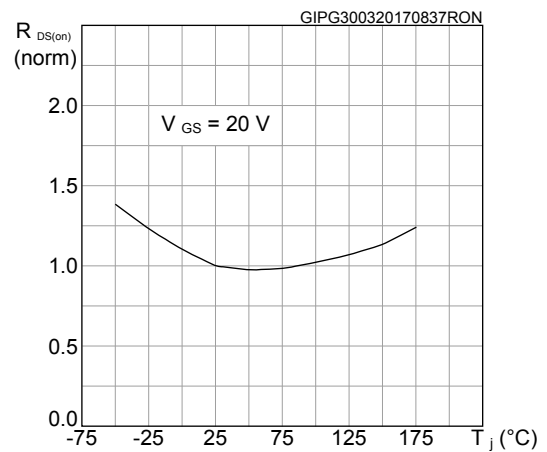


Figure 13. Body diode characteristics ( $T_J = -50^\circ\text{C}$ )

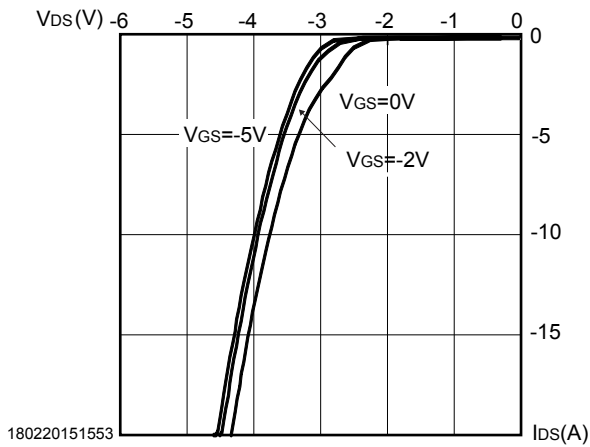


Figure 14. Body diode characteristics ( $T_J = 25^\circ\text{C}$ )

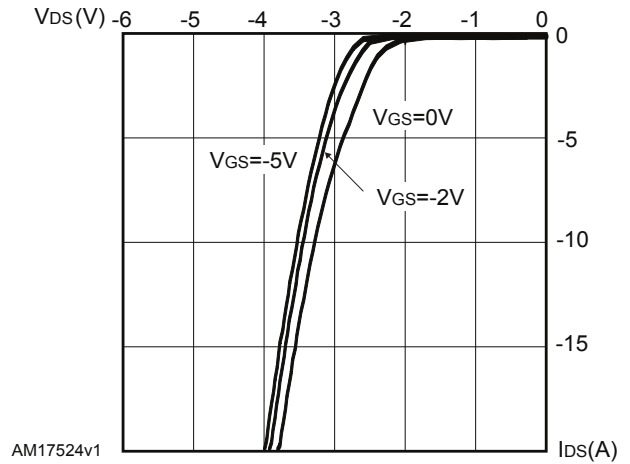


Figure 15. Body diode characteristics ( $T_J = 150^\circ\text{C}$ )

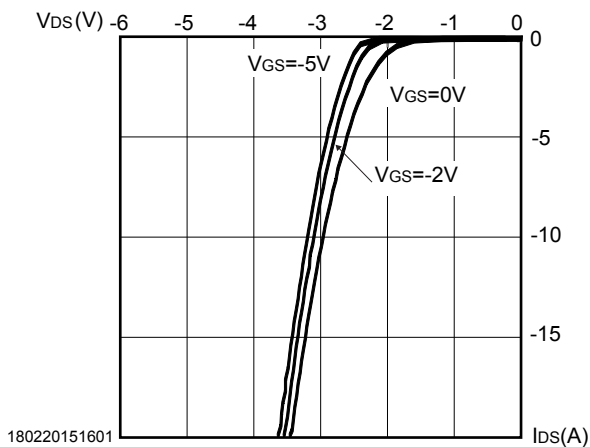


Figure 16. 3<sup>rd</sup> quadrant characteristics ( $T_J = -50^\circ\text{C}$ )

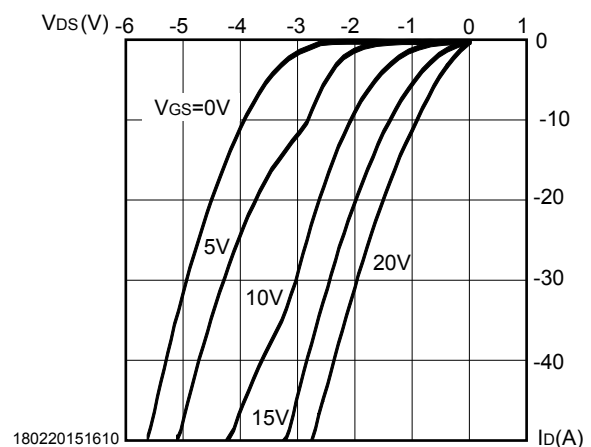


Figure 17. 3<sup>rd</sup> quadrant characteristics ( $T_J = 25^\circ\text{C}$ )

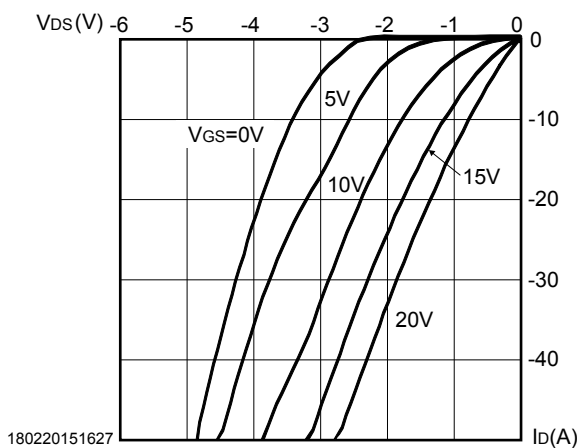
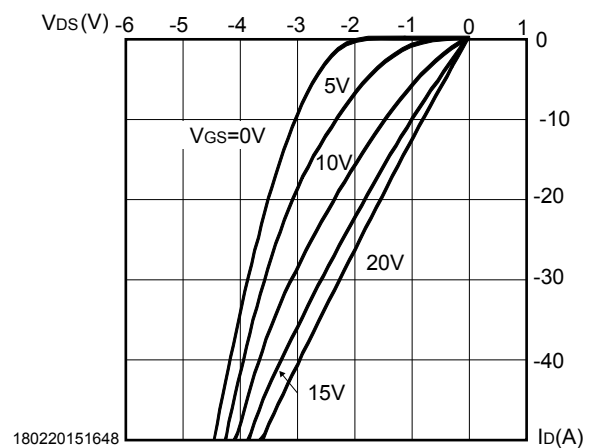
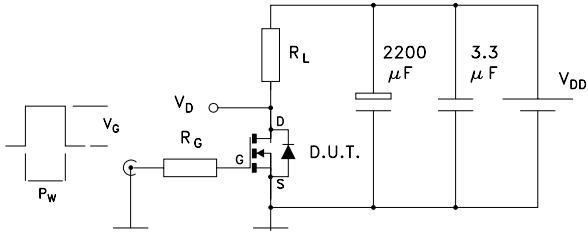


Figure 18. 3<sup>rd</sup> quadrant characteristics ( $T_J = 150^\circ\text{C}$ )



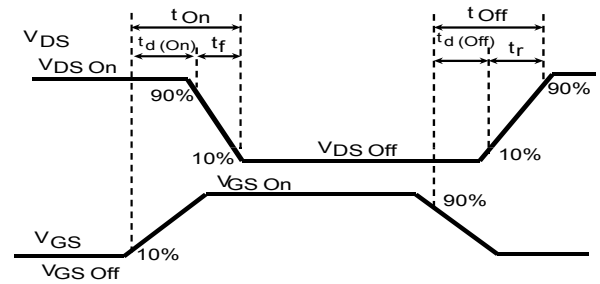
### 3 Test circuits

Figure 19. Switching test waveforms for transition times



GIPD101020141511FSR

Figure 20. Clamped inductive switching waveform



GIPD101020141502FSR

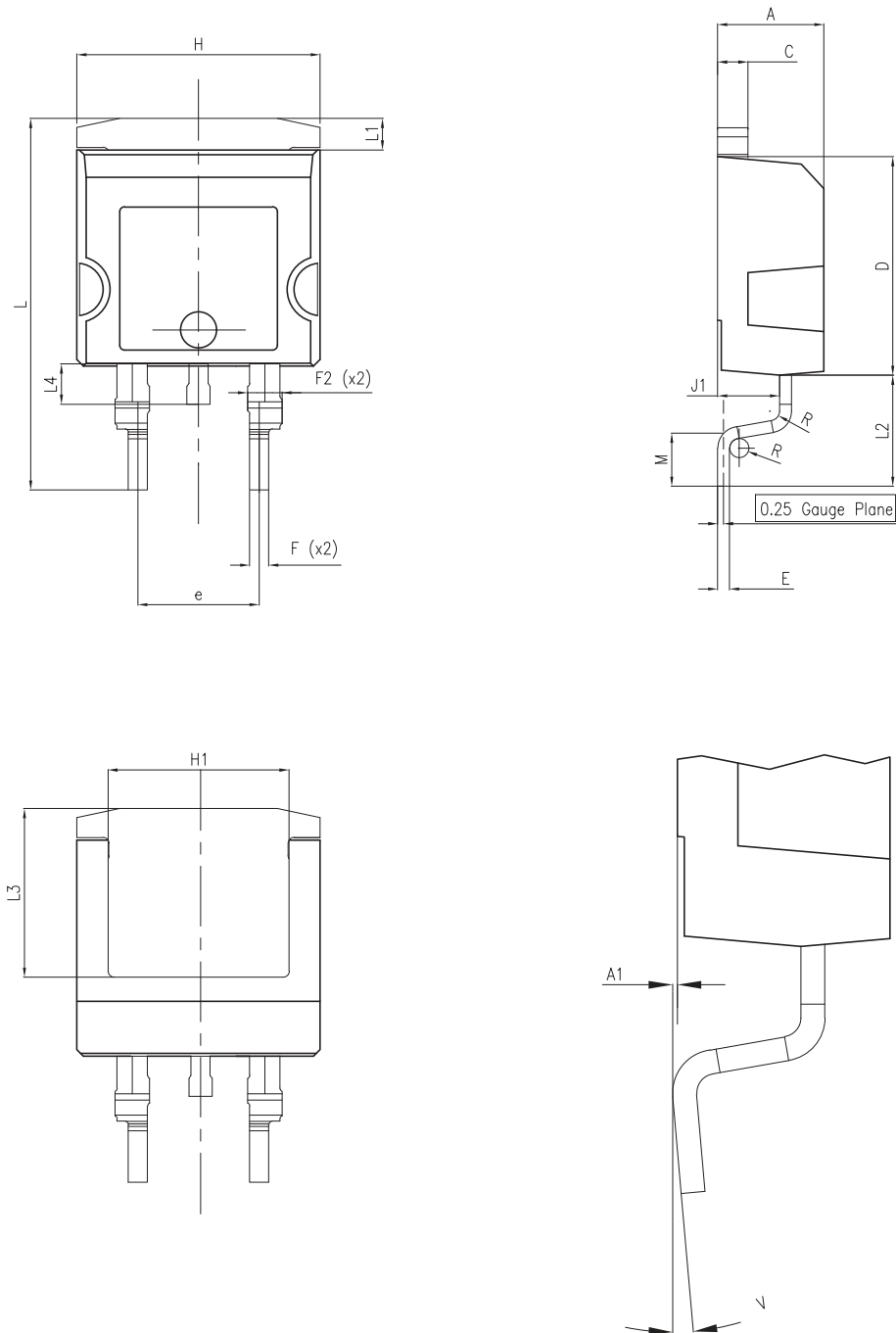


## 4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of **ECOPACK** packages, depending on their level of environmental compliance. ECOPACK specifications, grade definitions and product status are available at: [www.st.com](http://www.st.com). ECOPACK is an ST trademark.

### 4.1 H<sup>2</sup>PAK-2 package information

Figure 21. H<sup>2</sup>PAK-2 package outline

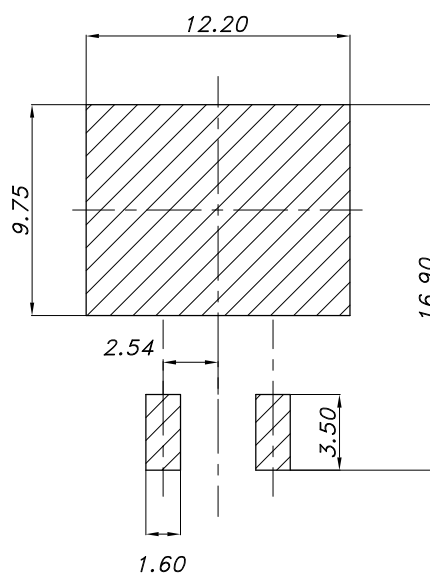


8159712\_9

Table 8. H<sup>2</sup>PAK-2 package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	4.30		4.70
A1	0.03		0.20
C	1.17		1.37
D	8.95		9.35
e	4.98		5.18
E	0.50		0.90
F	0.78		0.85
F2	1.14		1.70
H	10.00		10.40
H1	7.40	-	7.80
J1	2.49		2.69
L	15.30		15.80
L1	1.27		1.40
L2	4.93		5.23
L3	6.85		7.25
L4	1.50		1.70
M	2.60		2.90
R	0.20		0.60
V	0°		8°

Figure 22. H<sup>2</sup>PAK-2 recommended footprint

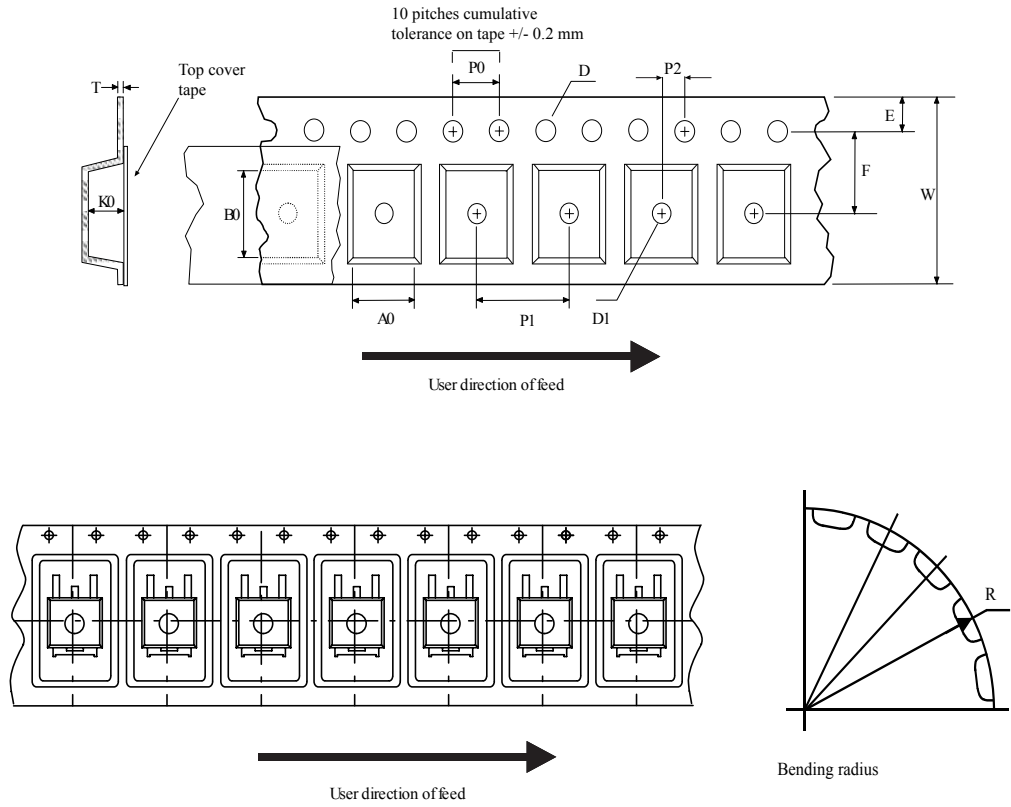


8159712\_9

Note: Dimensions are in mm.

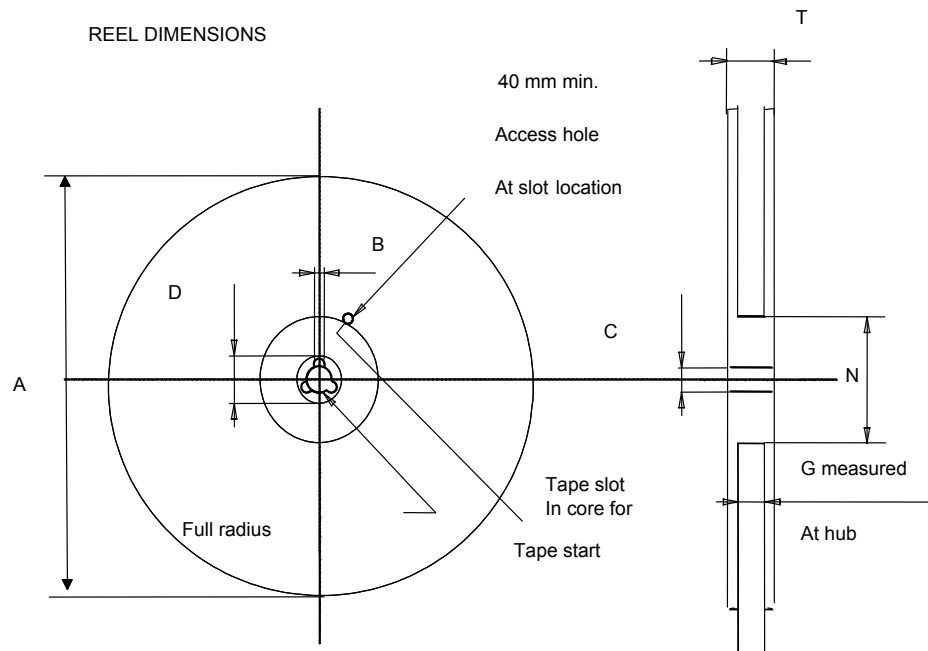
## 4.2 H<sup>2</sup>PAK-2 packing information

Figure 23. Tape outline



AM08852v2

**Figure 24. Reel outline**



**Table 9. Tape and reel mechanical data**

Dim.	Tape		Dim.	Reel	
	mm			mm	
	Min.	Max.		Min.	Max.
A0	10.5	10.7	A		330
B0	15.7	15.9	B	1.5	
D	1.5	1.6	C	12.8	13.2
D1	1.59	1.61	D	20.2	
E	1.65	1.85	G	24.4	26.4
F	11.4	11.6	N	100	
K0	4.8	5.0	T		30.4
P0	3.9	4.1			
P1	11.9	12.1	Base quantity		1000
P2	1.9	2.1	Bulk quantity		1000
R	50				
T	0.25	0.35			
W	23.7	24.3			

## Revision history

**Table 10. Document revision history**

Date	Revision	Changes
31-Jul-2015	1	First release
12-Oct-2015	2	Updated <i>Table 2</i> , <i>Table 3</i> and <i>Table 4</i> . Added <i>Figure 2: Safe operating area</i> .
01-Oct-2020	3	Updated features in cover page. Updated <a href="#">Section 1 Electrical ratings</a> , <a href="#">Section 2 Electrical characteristics</a> , <a href="#">Electrical characteristics (curves)</a> and <a href="#">Section 4.1 H<sup>2</sup>PAK-2 package information</a> . Added <a href="#">Section 3 Test circuits</a> . Minor text changes.

## Contents

<b>1</b>	<b>Electrical ratings</b> .....	<b>2</b>
<b>2</b>	<b>Electrical characteristics</b> .....	<b>3</b>
<b>2.1</b>	Electrical characteristics (curves) .....	<b>5</b>
<b>3</b>	<b>Test circuits</b> .....	<b>8</b>
<b>4</b>	<b>Package information</b> .....	<b>9</b>
<b>4.1</b>	H <sup>2</sup> PAK-2 package information .....	<b>9</b>
<b>4.2</b>	H <sup>2</sup> PAK-2 packing information .....	<b>11</b>
	<b>Revision history</b> .....	<b>13</b>

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